

μΑ715 High Speed Operational Amplifier

Linear Division Operational Amplifiers

Description

The μ A715 is a high speed, high gain, monolithic operational amplifier constructed using the Fairchild Planar Epitaxial process. It is intended for use in a wide range of applications where fast signal acquisition or wide bandwidth is required. The μ A715 features fast settling time, high slew rate, low offsets, and high output swing for large signal applications. In addition, the device displays excellent temperature stability and will operate over a wide range of supply voltages. The μ A715 is ideally suited for use in A/D and D/A converters, active filters, deflection amplifiers, video amplifiers, phase-locked loops, multiplexed analog gates, precision comparators, sample-and-holds, and general feedback applications requiring DC wide bandwidth operation.

- High Slew Rate 100 V/μs (Inverting, A_V = 1) Typically
- Fast Settling Time 800 ns Typically
- Wide Bandwidth 65 MHz Typically
- Wide Operating Supply Range
- Wide Input Voltage Ranges

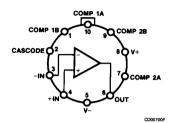
Absolute Maximum Ratings

Storage Temperature Range	-65°C to +175°C
Operating Temperature Range	
Extended (µA715M)	-55°C to +125°C
Commercial (µA715C)	0°C to +70°C
Lead Temperature	
Metal Can and Ceramic DIP	
(soldering, 60 s)	300°C
Internal Power Dissipation ^{1, 2}	
10L-Metal Can	1.07 W
14L-Ceramic DIP	1.36 W
Supply Voltage	± 18 V
Differential Input Voltage	± 15 V
Input Voltage ³	± 15 V

Notes

- 1. T_{J Max} = 175°C.
- Ratings apply to ambient temperature at 25°C. Above this temperature, derate the 10L-Metal Can at 7.1 mW/°C, and the 14L-Ceramic DIP at 9.1 mW/°C.
- 3. For supply voltages less than \pm 15 V, the absolute maximum input voltage is equal to the supply voltage.

Connection Diagram 10-Lead Metal Package (Top View)

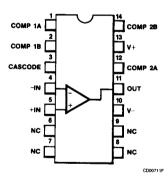


Lead 5 connected to case.

Order Information

Device Code	Package Code	Package Description
μΑ715HM	5X	Metal
μΑ715HC	5X	Metal

Connection Diagram 14-Lead DIP (Top View)

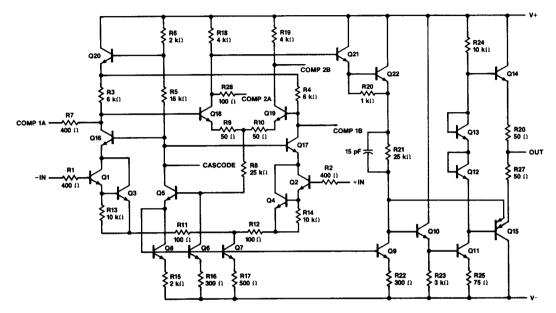


Order Information

Device Code	Package Code	Package Description
μA715DM	6A	Ceramic DIP
μA715DC	6A	Ceramic DIP

www.DataSheet.in

Equivalent Circuit



EQ00141F

www.DataSheet.in

 μA715 and μA715C Electrical Characteristics T_A = 25°C, V_{CC} = ± 15 V, unless otherwise specified.

	Characteristic	Condition	μ Α7 15			μ Α715C				
Symbol			Min	Тур	Max	Min	Тур	Max	Unit	
V _{IO}	Input Offset \	/oltage	R _S ≤ 10 kΩ		2.0	5.0		2.0	7.5	mV
l _{iO}	Input Offset (Current			70	250		70	250	nA
I _{IB}	Input Bias Cu	rrent			400	750		400	1500	nA
ZĮ	Input Impedar	nce			1.0			1.0		МΩ
Ro	Output Resist	ance			75			75		Ω
lcc	Supply Currer	ıt			5.5	7.0		5.5	10	mA
P _c	Power Consu	mption			165	210		165	300	mW
V _{IR}	Input Voltage	Range		± 10	± 12		± 10	± 12		V
A _{VS}	Large Signal	Voltage Gain	$R_L \ge 2.0 \text{ k}\Omega$, $V_O = \pm 10 \text{ V}$	15	30		10	30		V/mV
٧	Settling Time		$V_0 = \pm 5.0 \text{ V}, A_V = 1.0$		800			800		ns
TR	Transient	Rise time	$V_1 = 400 \text{ mV}, A_V = 1.0$		30	60		30	75	ns
	Response	Overshoot			25	40		25	50	%
SR	Slew Rate		A _V = 100		70		-	70		V/µs
			A _V = 10		38			38		
			A _V = 1.0 (non-inverting)	15	18		10	18		
			A _V = 1.0 (inverting)		100			100		

The following specifications apply over the range of $-55^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$ for the μA715 , and $0^{\circ}\text{C} \le \text{T}_{\text{A}} \le +70^{\circ}\text{C}$ for the μA715C .

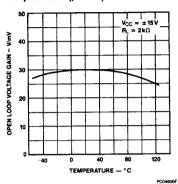
V _{IO}	Input Offset Voltage	$R_S \le 10 \text{ k}\Omega$			7.5			10	m۷
lio	Input Offset Current	$T_A = T_{A \text{ Max}}$			250			250	nA
		$T_A = T_{A \text{ Min}}$			800			750	
I _{IB}	Input Bias Current	$T_A = T_{A \text{ Max}}$			750			1500	nA
		T _A = T _{A Min}			4.0			7.5	
CMR	Common Mode Rejection	R _S ≤ 10 kΩ	74	92		74 ¹	92 ¹		db
PSRR	Power Supply Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$		45	300		45 ¹	400 ¹	μV/V
A _{VS}	Large Signal Voltage Gain	$R_L \ge 2.0 \text{ k}\Omega$, $V_O = \pm 10 \text{ V}$	10			8			V/mV
V _{OP}	Output Voltage Swing	$R_L = 2.0 \text{ k}\Omega$	±10	± 13		± 10	± 13		V

Note

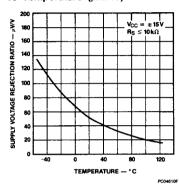
1. T_A = 25°C only.

Typical Performance Curves for μ A715 and μ A715C

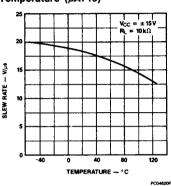
Voltage Gain vs Temperature (μΑ715)



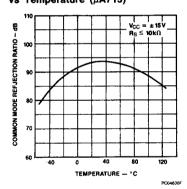
Supply Voltage Rejection Ratio vs Temperature (μΑ715)



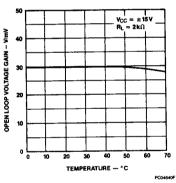
Siew Rate vs Temperature (µA715)



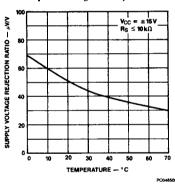
Common Mode Rejection Ratio vs Temperature (μ A715)



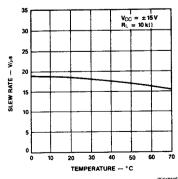
Voltage Gain vs Temperature (μΑ715C)



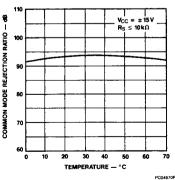
Supply Voltage Rejection Ratio vs Temperature (μΑ715C)



Slew Rate vs Temperature (μΑ715C)



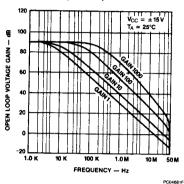
Common Mode Rejection Ratio vs Temperature (µA715C)



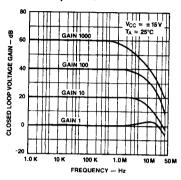
PC04670

Typical Performance Curves for μ A715 and μ A715C

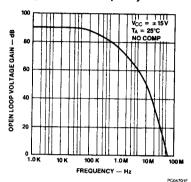
Frequency Response For Open Loop Gains (Note 1)



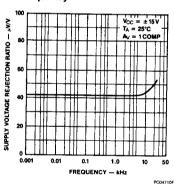
Frequency Response for Closed Loop Gains



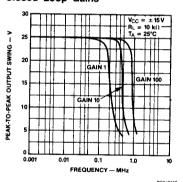
Voltage Gain vs Frequency



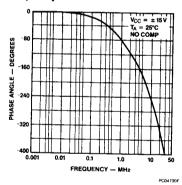
Supply Voltage Rejection Ratio vs Frequency



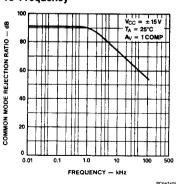
Output Swing vs Frequency for Closed Loop Gains



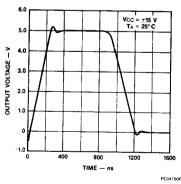
Open Loop Phase vs Frequency



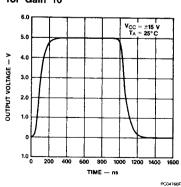
Common Mode Rejection Ratio vs Frequency



Unity Gain Large Signal Pulse Response



Large Signal Pulse Response for Gain 10



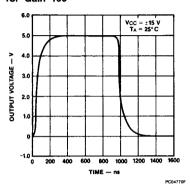
Note

1. See "Non-Inverting Compensation Components Value Table" for Closed Loop Gain values.

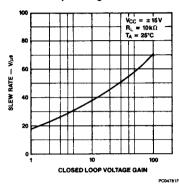
7

Typical Performance Curves for μ A715 and μ A715C (Cont.)

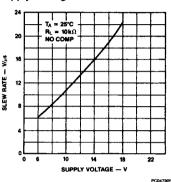
Large Signal Pulse Response for Gain 100



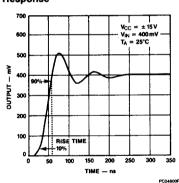
Slew Rate vs Closed Loop Voltage Gain



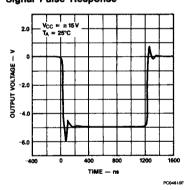
Slew Rate vs Supply Voltage



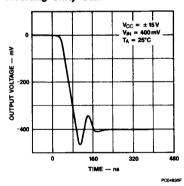
Voltage Follower Transient Response



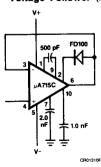
Inverting Unity Gain Large Signal Pulse Response



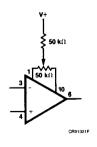
Small Signal Pulse Response Inverting Unity Gain



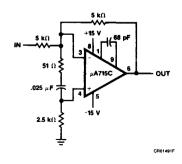
Voltage Follower (Note 1)



Voltage Offset Null Circuit (Note 1)



High Slew Rate Circuit (Note 1)



Note

Lead numbers apply to metal package.

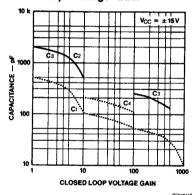
Non-Inverting Compensation Components Values

Closed Loop Gain	C 1	C2	C3
1000	10 pF		
100	50 pF		250 pF
10 (Note)	100 pF	500 pF	1000 pF
1	500 pF	2000 pF	1000 pF

Note

For gain 10, compensation may be simplified by removing C2, C3 and adding a 200 pF capacitor (C4) between Lead 7 and 10.

Suggested Values of Compensation Capacitors vs Closed Loop Voltage Gain



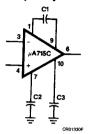
Layout Instructions

Layout — The layout should be such that stray capacitance is minimal.

Supplies — The supplies should be adequately bypassed. Use of 0.1 μF high quality ceramic capacitors is recommended.

Ringing — Excessive ringing (long acquisition time) may occur with large capacitive loads. This may be reduced by isolating the capacitive load with a resistance of 100 Ω .

Frequency Compensation Circuit



Note

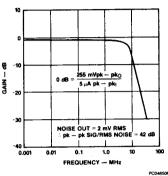
Lead numbers apply to metal package.

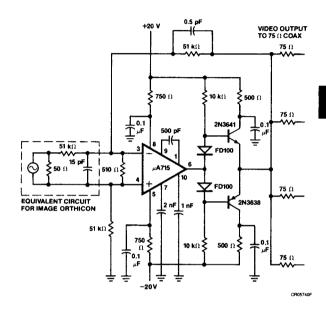
Large source resistances may also give rise to the same problem and this may be decreased by the addition of a capacitance across the feedback resistance. A value of around 50 pF for unity gain configuration and around 3.0 pF for gain 10 should be adequate.

Latch Up — This may occur when the amplifier is used as a voltage follower. The inclusion of a diode between leads 6 and 2 with the cathode toward lead 2 is the recommended preventive measure.

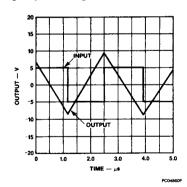
Typical Applications

Wide Bank Video Amplifier Drive Capability With 75 Ω Coax Cable





High Speed Integrator



Note All lead numbers shown refer to metal package.

